

## AMENDMENTS TO THE CLAIMS

Claims 1-6. (Canceled)

7. (Currently Amended) The ~~thin-film resistor of claim 6~~ structure of claim 18, wherein said dielectric layer comprises silicon nitride.
8. (Currently Amended) The ~~thin-film resistor~~ structure of claim 7, wherein said dielectric layer has a thickness of from about 65 nm to about 75 nm.

Claims 9-17. (Canceled)

18. (Previously Presented) A semiconductor structure comprising:
  - a substrate comprising a plurality of interconnects formed on an upper surface of an inter-metal dielectric layer; and
  - a thin-film resistor comprising a conductor layer formed on the upper surface of said inter-metal dielectric layer and adjacent to a first of said plurality of interconnects, said conductor layer comprising end portions tapered at a constant angle between about 20 degrees to about 70 degrees with respect to the upper surface to provide contact regions; a dielectric layer formed on said conductor layer; and contacts abutting said contact regions to provide for electrical coupling to said thin-film resistor.
19. (Original) The structure of claim 18, wherein said conductor layer comprises tantalum nitride.
20. (Original) The structure of claim 18, wherein said plurality of interconnects comprise aluminum or aluminum alloys.